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Model Bug Fixes for BSIM4.2.1

- ❖ 1/f noise model bug fix
- ❖ Memory pointer bug
- ❖ ACDE check
- ❖ Temperature parameters for parasitic diodes
- ❖ Bug fix for narrow width effect
- ❖ Addition of Gate Induced Source Leakage
- ❖ L,W,Tox parameter warning limit checking



1/f Noise Model Bug Fix

Requested by David Zweidinger Keith Green Britt Brooks

Texas Instruments

Problem: negative DelCIm under certain conditions of voltage bias, temperature, L, and W

$$S_{id,inv}(f) = \frac{k_B T q^2 m_{eff} I_{ds}}{C_{oxe} L_{eff}^2 A_{bulk} f^{ef} \cdot 10^0} \left(NOIA \log \left(\frac{N_0 + N^*}{N_l + N^*} \right) + NOIB(N_0 - N_l) + \frac{NOIC}{2} (N_0^2 - N_l^2) \right)$$

$$+ \frac{k_B T I_{ds}^2 \Delta L}{W_{eff} \cdot L_{eff}^2 f^{ef} \cdot 10^0} \cdot \frac{clm \cdot NOIA + NOIB N_l + NOIC N_l^2}{(N_l + N^*)^2}$$

$$\Delta L_{clm} = Litl \cdot \log \left(\frac{V_{ds} - V_{dseff} + EM}{E_{sat}} \right)$$

$$E_{sat} = \frac{2VSAT}{m_{eff}}$$

In b4noi.c:

```
if(model->BSIM4em<=0.0) DelCIm = 0.0; /* flicker noise modified -JX */
else {
    T0 = (((Vds - here->BSIM4Vdseff) / pParam->BSIM4litl)
          + model->BSIM4em) / esat);
    DelCIm = pParam->BSIM4litl * log (MAX(T0, N_MINLOG));
}
```



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Memory Pointer Bug

Requested by David Zweidinger Keith Green Britt Brooks

Texas Instruments

Problem: No value assignment to pParam for no-binning approach.

In b4temp.c:

```
while ((pSizeDependParamKnot != NULL) && Size_Not_Found)
{ if ((here->BSIM4l == pSizeDependParamKnot->Length)
    && (here->BSIM4w == pSizeDependParamKnot->Width)
    && (here->BSIM4nf == pSizeDependParamKnot->NFinger))
{ Size_Not_Found = 0;
  here->pParam = pSizeDependParamKnot;
  pParam = here->pParam; /*bug-fix */
}
}
```

Jane Xi, October 05,2001



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ACDE (capMod 2) Checking

Requested by David Zweidinger Keith Green Britt Brooks

Texas Instruments

Problem: warning message for other capacitance models

In b4check.c:

```
if(model->BSIM4capMod ==2) {  
    if (pParam->BSIM4acde < 0.4)  
    { fprintf(fplog, "Warning: Acde = %g is too small.\n", pParam->BSIM4acde);  
      printf("Warning: Acde = %g is too small.\n", pParam->BSIM4acde);  
    }  
    if (pParam->BSIM4acde > 1.6)  
    { fprintf(fplog, "Warning: Acde = %g is too large.\n", pParam->BSIM4acde);  
      printf("Warning: Acde = %g is too large.\n", pParam->BSIM4acde);  
    }  
}
```

Jane Xi, October 05,2001



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Temperature Parameters for Parasitic Diodes

Requested by Alex Zavorine

Circuit Semantics

Jane Xi

UC Berkeley

Problems: Model parameters be reassigned with new value for parasitic diode parameters in b4temp.c

In bsim4def.h, new Pre-calculated constants added:

```
double BSIM4SunitAreaTempJctCap;  
double BSIM4DunitAreaTempJctCap;  
double BSIM4SunitLengthSidewallTempJctCap;  
double BSIM4DunitLengthSidewallTempJctCap;  
double BSIM4SunitLengthGateSidewallTempJctCap;  
double BSIM4DunitLengthGateSidewallTempJctCap;
```

Modifications needed in bsim4def.h, b4temp.c, b4ld.c.



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Bug Fix for Narrow Width Effect

Requested by Mark Cao Jane Xi UC Berkeley

In b4ld.c:

```
T0 = pParam->BSIM4dvt1w * pParam->BSIM4weff * Leff / ltw;  
if (T0 < EXP_THRESHOLD)  
{ T1 = exp(T0);  
  T2 = T1 - 1.0;  
  T3 = T2 * T2;  
  T4 = T3 + 2.0 * T1 * MIN_EXP;  
  T5 = T1 / T4;  
  
  dT1_dVb = -T0 * T1 * dltw_dVb / ltw; /* bug fix -JX */  
  dT5_dVb = dT1_dVb * (T4 - 2.0 * T1 * (T2 + MIN_EXP)) / T4 / T4;  
}
```



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Addition of GISL(Gate Induced Source Leakage) in BSIM4 (bug fix)

Requested by David Zweidinger Keith Green Britt Brooks
Tom Vrotsos Vinod Gupta John Krick
Texas Instruments

Advantage: an enormous impact on circuit simulation convergence

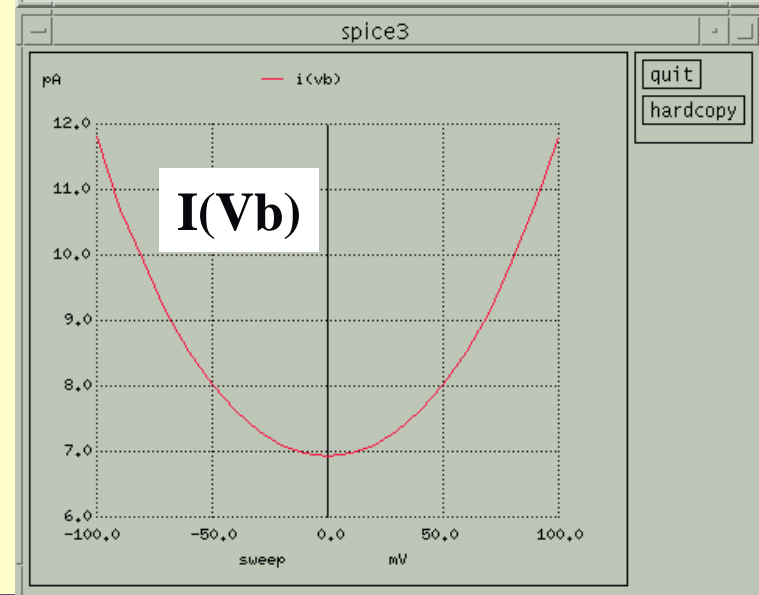
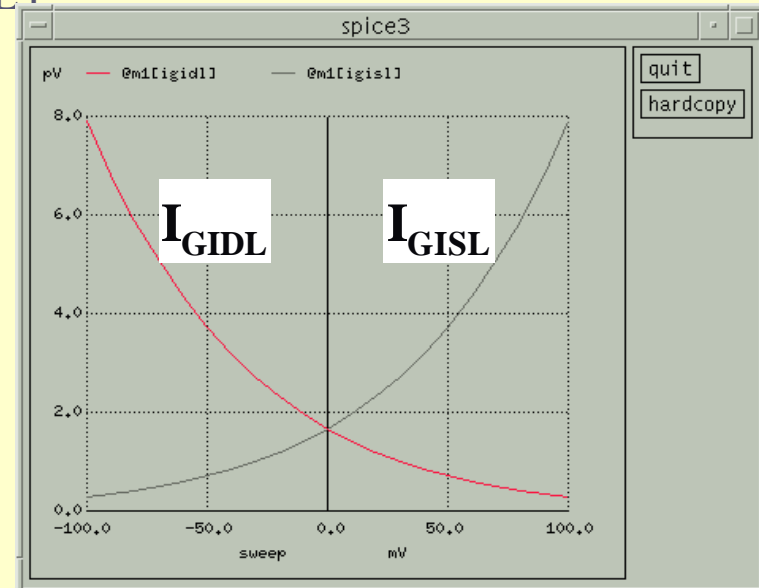
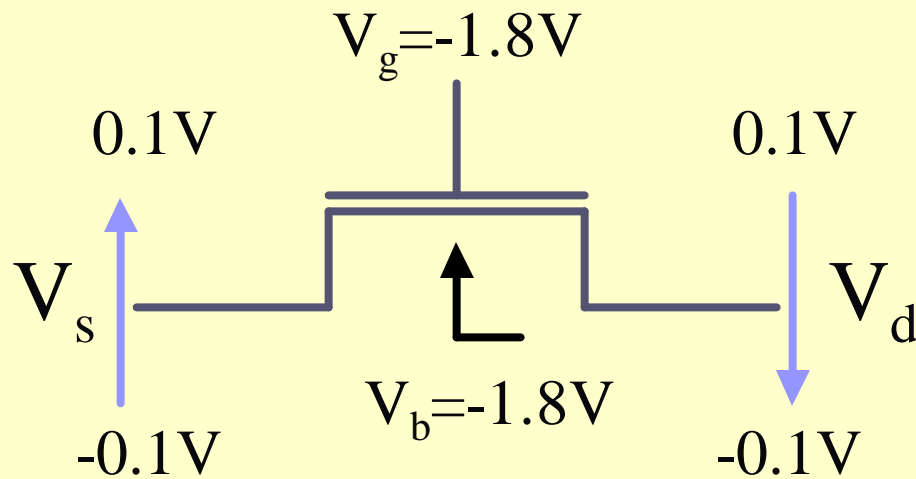
Follow the same model of I_{GIDL} :

$$I_{GISL} = AGIDL \cdot W_{effCJ} \cdot Nf \cdot \frac{-V_{ds} - V_{gde} - EGIDL}{3 \cdot T_{oxe}} \cdot \exp\left(\frac{3 \cdot T_{oxe} \cdot BGIDL}{-V_{ds} - V_{gde} - EGIDL}\right) \cdot \frac{V_{sb}^3}{CGIDL + V_{sb}^3}$$

Modifications needed in b4ld.c, b4acl.c, b4pzld.c, b4cvtest.c



Gummel's Symmetry Test for GIDL & GISL





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L,W,Tox Parameter Warning Limit

Requested by David Zweidinger Keith Green Britt Brooks

Texas Instruments

	Original	Now	Recommended
Leff (m)	5e-8	1e-9	1e-8
Leffcv (m)	5e-8	1e-9	1e-8
Weff (m)	1e-7	1e-9	1e-7
Weffcv (m)	1e-7	1e-9	1e-7
Toxe (m)	1e-9	1e-10	5e-10
Toxp (m)	1e-9	1e-10	5e-10
Toxm (m)	1e-9	1e-10	5e-10

- If(L,W,Tox <=0) {fatal message; Fatal_Flag =1;}
- If(L,W,Tox < warning limit) {warning messages;}
- Recommended value here are for a meanful output from BSIM4

Jane Xi, October 05,2001